

isc Silicon PNP Power Transistor

BUP40

DESCRIPTION

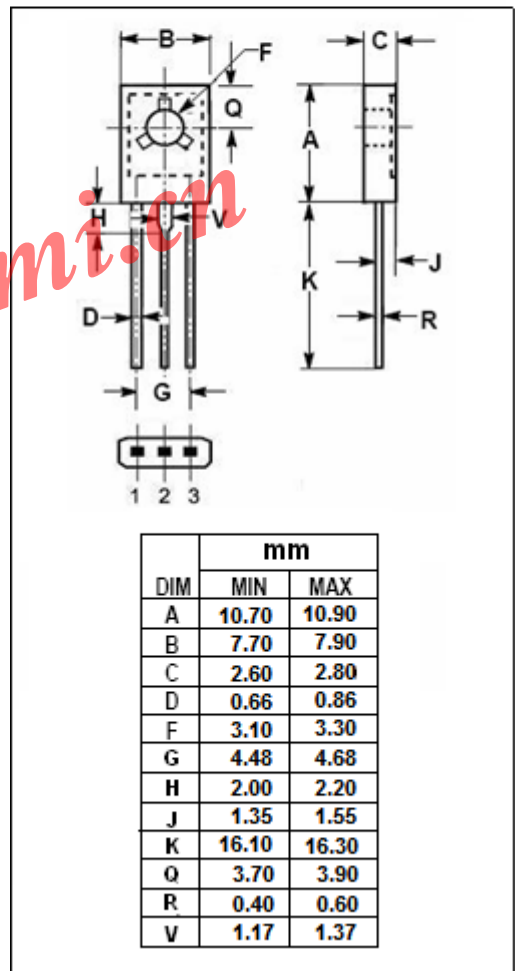
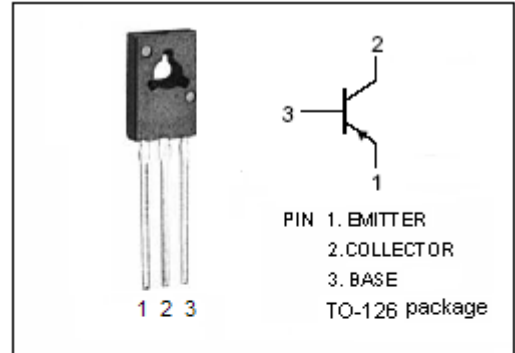
- High Collector Current- $I_C = -6A$
- Low Collector Saturation Voltage -
: $V_{CE(sat)} = -0.4V(\text{Max}) @ I_C = 3A, I_B = -0.1A$
- High Switching Speed
- Complement to Type BUP41

APPLICATIONS

- For audio amplifier and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emmitter Voltage	-50	V
V_{EBO}	Emmitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-6	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	10	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**BUP40****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -3A; I_B = -0.1A$			-1.1	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -3A; I_B = -0.1A$			-1.4	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -40V; I_E = 0$			-1.0	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4V; I_C = 0$			-1.0	μA
h_{FE-1}	DC Current Gain	$I_C = -1A; V_{CE} = -2V$	100		500	
h_{FE-2}	DC Current Gain	$I_C = -5A; V_{CE} = -5V$	40			
f_T	Current-Gain—Bandwidth Product	$I_C = -1A; V_{CE} = -5V$		150		MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10V$		40		pF

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